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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2824
	Examiner Name	Unknown HIEN NGUYEN
Sheet 1 of 1		Attorney Docket No: 303.620US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ⁴
HN		EITAN, BOAZ, "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell", <u>IEEE Electron Device Letters</u> , 21(11), (November 2000), 543-545		
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EXAMINER

HIEN NGUYEN

DATE CONSIDERED

3/19/04

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.¹ Applicant's unique citation designation number (optional) ² Applicant is to place a check mark here if English language Translation is attached